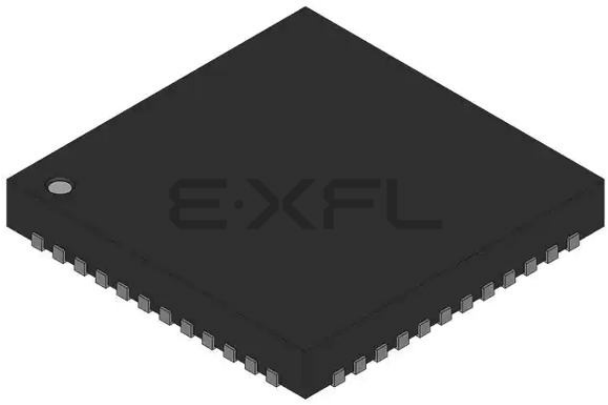

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	50MHz
Connectivity	I²C, LINbus, SCI, SPI
Peripherals	LVD, PWM, WDT
Number of I/O	38
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-VFQFN Exposed Pad
Supplier Device Package	48-QFN-EP (7x7)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mc9s08qe96cft

Table of Contents

1 MC9S08QE128 Series Comparison

The following table compares the various device derivatives available within the MC9S08QE128 series.

Table 1. MC9S08QE128 Series Features by MCU and Package

Feature	MC9S08QE128				MC9S08QE96				MC9S08QE64			
Flash size (bytes)	131072				98304				65536			
RAM size (bytes)	8064				6016				4096			
Pin quantity	80	64	48	44	80	64	48	44	64	48	44	32
ACMP1	yes											
ACMP2	yes											
ADC channels	24	22	10	10	24	22	10	10	22	10	10	10
DBG	yes											
ICS	yes											
IIC1	yes											
IIC2	yes	yes	no	no	yes	yes	no	no	yes	no	no	no
IRQ	yes											
KBI	16	16	16	16	16	16	16	16	16	16	16	12
Port I/O[1]	70	54	38	34	70	54	38	34	54	38	34	26
RTC	yes											
SCI1	yes											
SCI2	yes											
SPI1	yes											
SPI2	yes											
TPM1 channels	3											
TPM2 channels	3											
TPM3 channels	6											
XOSC	yes											

[1] Port I/O count does not include the input only PTA5/IRQ/TPM1CLK/$\overline{\text{RESET}}$ or the output only PTA4/ACMP1O/BKGD/MS.

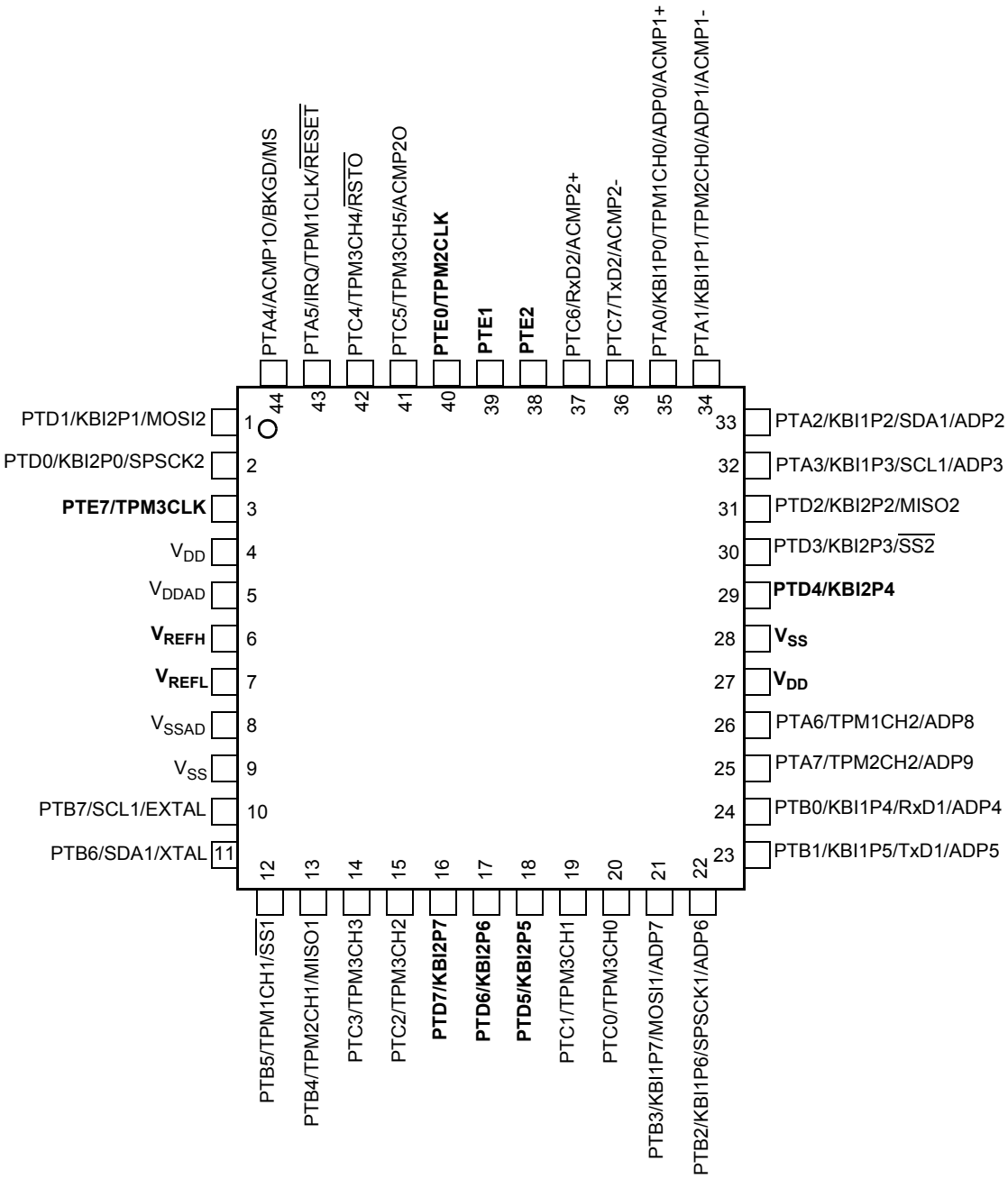


Figure 5. Pin Assignments in 44-Pin LQFP Package

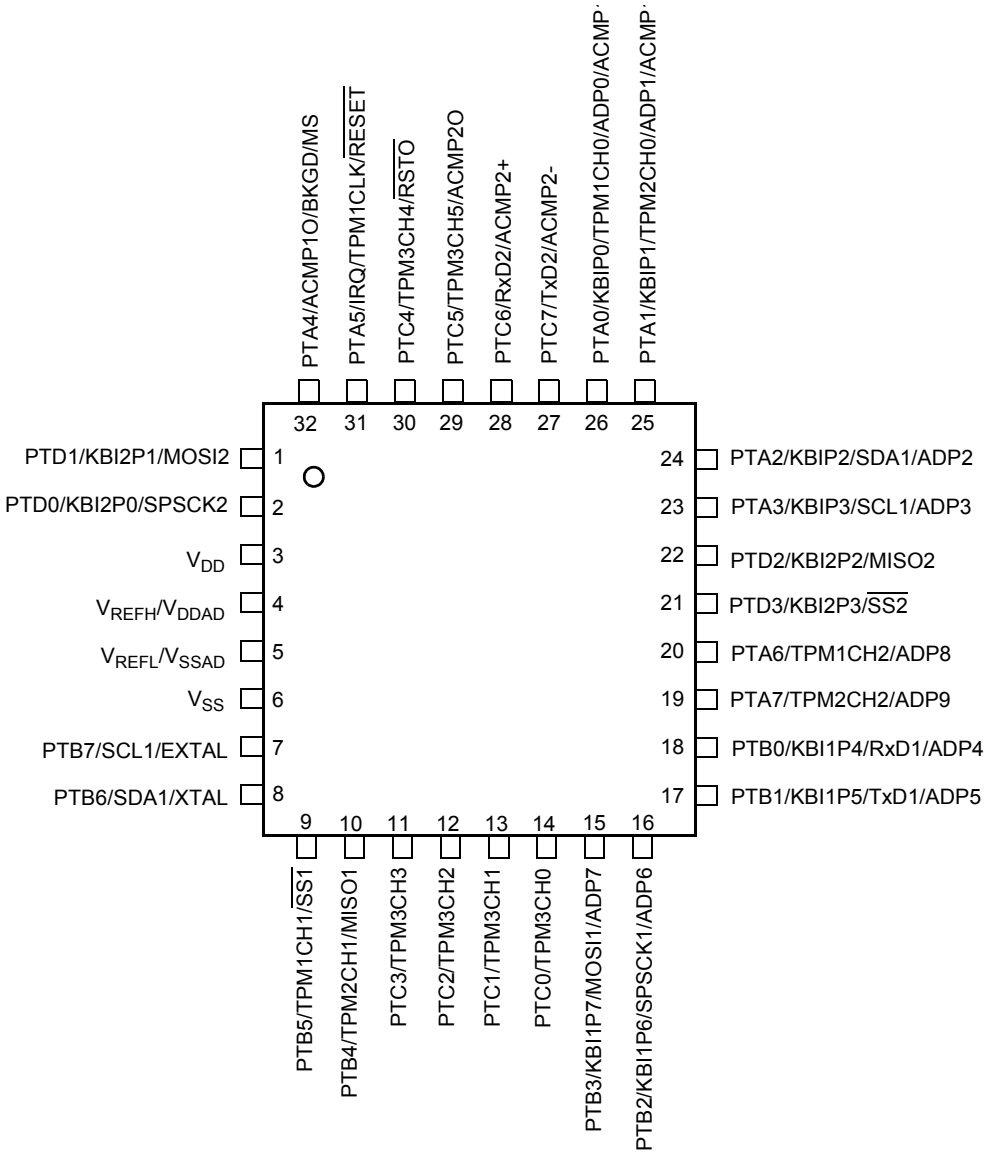


Figure 6. Pin Assignments 32-Pin LQFP Package

[3] Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low (which would reduce overall power consumption).

3.4 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 5. Thermal Characteristics

Rating	Symbol	Value	Unit
Operating temperature range (packaged)	T_A	–40 to 85	°C
Maximum junction temperature	T_{JM}	95	°C
Thermal resistance Single-layer board			
32-pin LQFP	θ_{JA}	82	°C/W
44-pin LQFP		68	
48-pin QFN		81	
64-pin LQFP	θ_{JA}	69	°C/W
80-pin LQFP		60	
Thermal resistance Four-layer board			
32-pin LQFP	θ_{JA}	54	°C/W
44-pin LQFP		46	
48-pin QFN		26	
64-pin LQFP	θ_{JA}	50	°C/W
80-pin LQFP		47	

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \qquad \textit{Eqn. 1}$$

where:

T_A = Ambient temperature, °C
θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W
$P_D = P_{int} + P_{I/O}$
$P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power
$P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273°C) \quad \textit{Eqn. 2}$$

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273°C) + \theta_{JA} \times (P_D)^2 \quad \textit{Eqn. 3}$$

where K is a constant pertaining to the particular part. K can be determined from equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving Equation 1 and Equation 2 iteratively for any value of T_A.

3.5 ESD Protection and Latch-Up Immunity

Although damage from electrostatic discharge (ESD) is much less common on these devices than on early CMOS circuits, normal handling precautions should be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits. During the device qualification ESD stresses were performed for the human body model (HBM), the machine model (MM) and the charge device model (CDM).

A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 6. ESD and Latch-up Test Conditions

Model	Description	Symbol	Value	Unit
Human Body	Series resistance	R1	1500	Ω
	Storage capacitance	C	100	pF
	Number of pulses per pin	—	3	
Machine	Series resistance	R1	0	Ω
	Storage capacitance	C	200	pF
	Number of pulses per pin	—	3	
Latch-up	Minimum input voltage limit		– 2.5	V
	Maximum input voltage limit		7.5	V

Table 7. ESD and Latch-Up Protection Characteristics

No.	Rating[1]	Symbol	Min	Max	Unit
1	Human body model (HBM)	V_{HBM}	± 2000	—	V
2	Machine model (MM)	V_{MM}	± 200	—	V
3	Charge device model (CDM)	V_{CDM}	± 500	—	V
4	Latch-up current at T_A = 85°C	I_{LAT}	± 100	—	mA

1 Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

3.6 DC Characteristics

This section includes information about power supply requirements and I/O pin characteristics.

Table 8. DC Characteristics

Num	C	Characteristic	Symbol	Condition	Min	Typ[1]	Max	Unit
1		Operating Voltage			1.8[2]		3.6	V
2	C	Output high voltage — All I/O pins, low-drive strength	V_{OH}	1.8 V, I_{Load} = –2 mA	V_{DD} – 0.5	—	—	V
	P	Output high voltage — All I/O pins, high-drive strength		2.7 V, I_{Load} = –10 mA	V_{DD} – 0.5	—	—	
	T			2.3 V, I_{Load} = –6 mA	V_{DD} – 0.5	—	—	
	C			1.8V, I_{Load} = –3 mA	V_{DD} – 0.5	—	—	
3	D	Output high current — Max total I_{OH} for all ports	I_{OHT}		—	—	100	mA
4	C	Output low voltage — All I/O pins, low-drive strength	V_{OL}	1.8 V, I_{Load} = 2 mA	—	—	0.5	V
	P	Output low voltage — All I/O pins, high-drive strength		2.7 V, I_{Load} = 10 mA	—	—	0.5	
	T			2.3 V, I_{Load} = 6 mA	—	—	0.5	
	C			1.8 V, I_{Load} = 3 mA	—	—	0.5	
5	D	Output low current — Max total I_{OL} for all ports	I_{OLT}		—	—	100	mA
6	P	Input high voltage — all digital inputs	V_{IH}	V_{DD} > 2.7 V	0.70 x V_{DD}	—	—	V
	C			V_{DD} > 1.8 V	0.85 x V_{DD}	—	—	
7	P	Input low voltage — all digital inputs	V_{IL}	V_{DD} > 2.7 V	—	—	0.35 x V_{DD}	
	C			V_{DD} >1.8 V	—	—	0.30 x V_{DD}	
8	C	Input hysteresis — all digital inputs	V_{hys}		0.06 x V_{DD}	—	—	mV
9	P	Input leakage current — all input only pins (Per pin)	$\|I_{In}\|$	V_{In} = V_{DD} or V_{SS}	—	—	1	µA
10	P	Hi-Z (off-state) leakage current — all input/output (per pin)	$\|I_{OZ}\|$	V_{In} = V_{DD} or V_{SS}	—	—	1	µA
11	P	Pull-up resistors — all digital inputs, when enabled	R_{PU}		17.5	—	52.5	kΩ
12	D	DC injection current [3, 4, 5] — Single pin limit	I_{IC}	V_{IN} < V_{SS}, V_{IN} > V_{DD}	–0.2	—	0.2	mA
		DC injection current [3, 4, 5] — Total MCU limit, includes sum of all stressed pins			–5	—	5	mA
13	C	Input Capacitance, all pins	C_{In}		—	—	8	pF
14	C	RAM retention voltage	V_{RAM}		—	0.6	1.0	V
15	C	POR re-arm voltage[6]	V_{POR}		0.9	1.4	1.79	V
16	D	POR re-arm time	t_{POR}		10	—	—	µs
17	P	Low-voltage detection threshold — high range[7]	V_{LVDH}[8]	V_{DD} falling V_{DD} rising	2.11 2.16	2.16 2.21	2.22 2.27	V

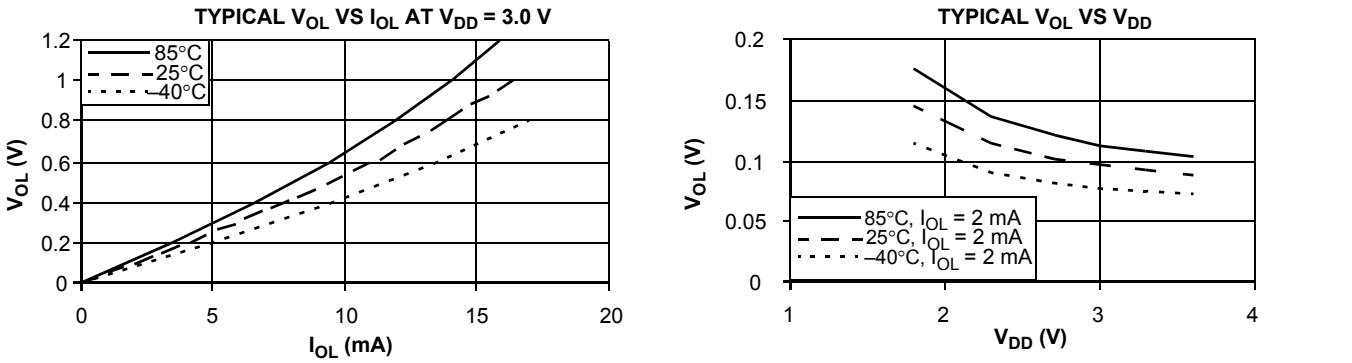


Figure 8. Typical Low-Side Driver (Sink) Characteristics — Low Drive (PTxDSn = 0)

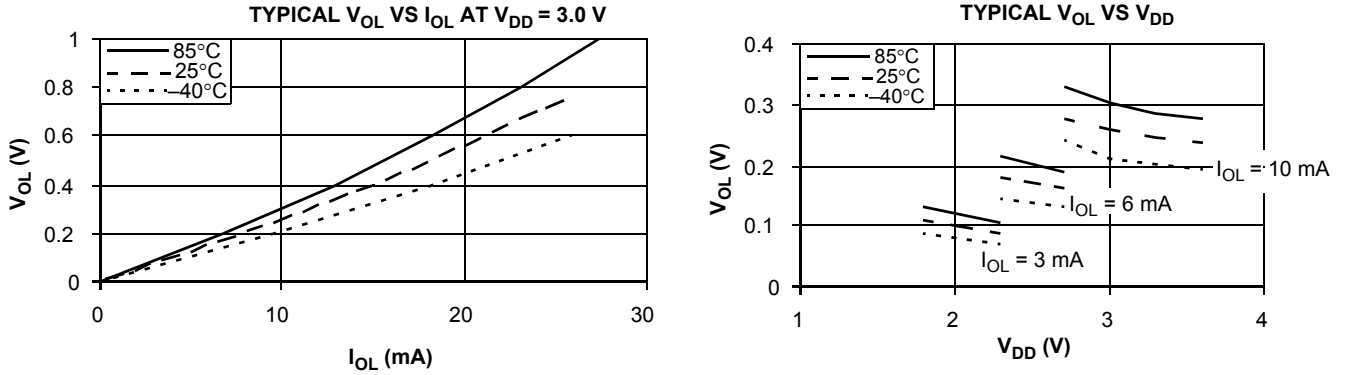


Figure 9. Typical Low-Side Driver (Sink) Characteristics — High Drive (PTxDSn = 1)

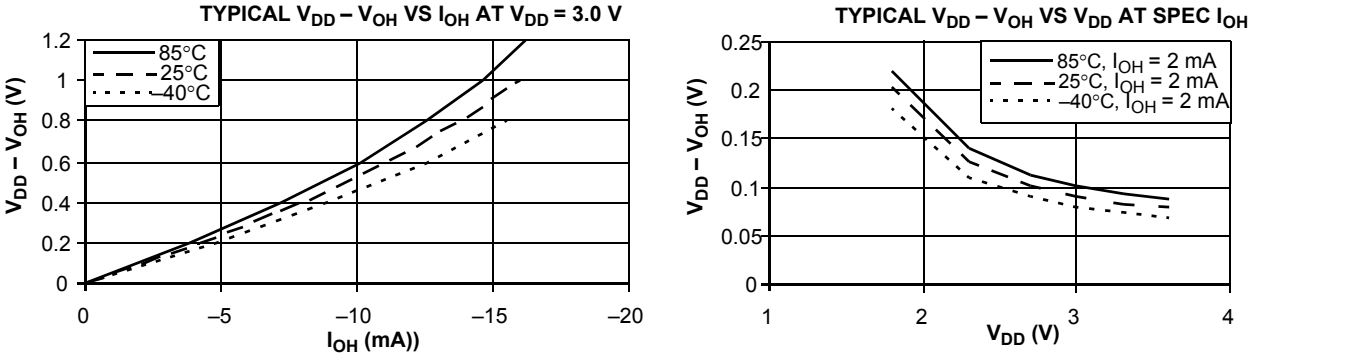


Figure 10. Typical High-Side (Source) Characteristics — Low Drive (PTxDSn = 0)

3.8 External Oscillator (XOSC) Characteristics

Reference Figure 13 and Figure 14 for crystal or resonator circuits.

Table 11. XOSC and ICS Specifications (Temperature Range = –40 to 85°C Ambient)

Num	C	Characteristic	Symbol	Min	Typ[1]	Max	Unit
1	C	Oscillator crystal or resonator (EREFS = 1, ERCLKEN = 1) Low range (RANGE = 0) High range (RANGE = 1), high gain (HGO = 1) High range (RANGE = 1), low power (HGO = 0)	 f_{lo} f_{hi} f_{hi}	 32 1 1	 — — —	 38.4 16 8	 kHz MHz MHz
2	D	Load capacitors Low range (RANGE=0), low power (HGO=0) Other oscillator settings	C_1,C_2	See Note[2] See Note[3]			
3	D	Feedback resistor Low range, low power (RANGE=0, HGO=0)[2] Low range, High Gain (RANGE=0, HGO=1) High range (RANGE=1, HGO=X)	R_F	 — — —	 — 10 1	 — — —	MΩ
4	D	Series resistor — Low range, low power (RANGE = 0, HGO = 0)[2] Low range, high gain (RANGE = 0, HGO = 1) High range, low power (RANGE = 1, HGO = 0) High range, high gain (RANGE = 1, HGO = 1) ≥ 8 MHz 4 MHz 1 MHz	R_S	 — — — — — —	 — 0 100 0 0 0	 — — — 0 10 20	kΩ
5	C	Crystal start-up time [4] Low range, low power Low range, high power High range, low power High range, high power	 t_{CSTL} t_{CSTH} 	 — — — —	 200 400 5 15	 — — — —	ms
6	D	Square wave input clock frequency (EREFS = 0, ERCLKEN = 1) FEE or FBE mode FBELP mode	f_{extal}	0.03125 0	— —	40.0 50.33	MHz MHz

1 Data in Typical column was characterized at 3.0 V, 25°C or is typical recommended value.

2 Load capacitors (C_1,C_2), feedback resistor (R_F) and series resistor (R_S) are incorporated internally when RANGE=HGO=0.

3 See crystal or resonator manufacturer's recommendation.

4 Proper PC board layout procedures must be followed to achieve specifications.

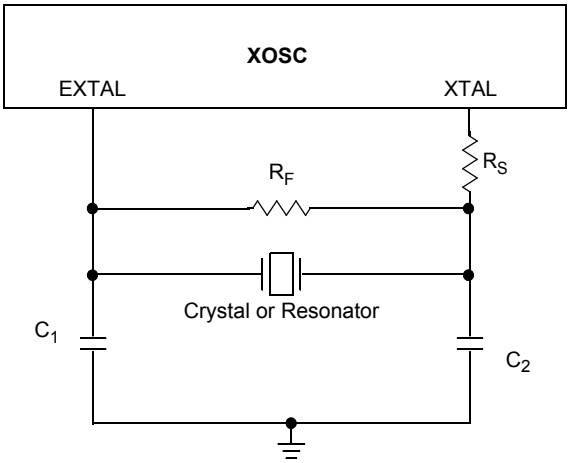


Figure 13. Typical Crystal or Resonator Circuit: High Range and Low Range/High Gain

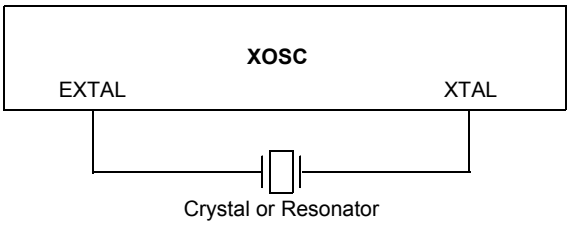


Figure 14. Typical Crystal or Resonator Circuit: Low Range/Low Gain

3.9 Internal Clock Source (ICS) Characteristics

Table 12. ICS Frequency Specifications (Temperature Range = –40 to 85°C Ambient)

Num	C	Characteristic		Symbol	Min	Typ[1]	Max	Unit
1	P	Average internal reference frequency — factory trimmed at V_{DD} = 3.6 V and temperature = 25°C		f_{int_ft}	—	32.768	—	kHz
2	P	Internal reference frequency — user trimmed		f_{int_ut}	31.25	—	39.06	kHz
3	T	Internal reference start-up time		t_{IRST}	—	60	100	µs
4	P	DCO output frequency range — trimmed [2]	Low range (DRS=00)	f_{dco_u}	16	—	20	MHz
	P		Mid range (DRS=01)		32	—	40	
	P		High range (DRS=10)		48	—	60	
5	P	DCO output frequency [2] Reference = 32768 Hz and DMX32 = 1	Low range (DRS=00)	f_{dco_DMX32}	—	19.92	—	MHz
	P		Mid range (DRS=01)		—	39.85	—	
	P		High range (DRS=10)		—	59.77	—	
6	C	Resolution of trimmed DCO output frequency at fixed voltage and temperature (using FTRIM)		$\Delta f_{dco\_res\_t}$	—	± 0.1	± 0.2	$\%f_{dco}$
7	C	Resolution of trimmed DCO output frequency at fixed voltage and temperature (not using FTRIM)		$\Delta f_{dco\_res\_t}$	—	± 0.2	± 0.4	$\%f_{dco}$

Table 12. ICS Frequency Specifications (Temperature Range = –40 to 85°C Ambient) (continued)

Num	C	Characteristic	Symbol	Min	Typ[1]	Max	Unit
8	C	Total deviation of trimmed DCO output frequency over voltage and temperature	Δf_{dco_t}	—	+ 0.5 -1.0	± 2	$\%f_{dco}$
9	C	Total deviation of trimmed DCO output frequency over fixed voltage and temperature range of 0°C to 70 °C	Δf_{dco_t}	—	± 0.5	± 1	$\%f_{dco}$
10	C	FLL acquisition time [3]	$t_{Acquire}$	—	—	1	ms
11	C	Long term jitter of DCO output clock (averaged over 2-ms interval) [4]	C_{Jitter}	—	0.02	0.2	$\%f_{dco}$

1 Data in Typical column was characterized at 3.0 V, 25°C or is typical recommended value.

2 The resulting bus clock frequency should not exceed the maximum specified bus clock frequency of the device.

3 This specification applies to any time the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (FBELP, FBILP) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

4 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{Bus}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

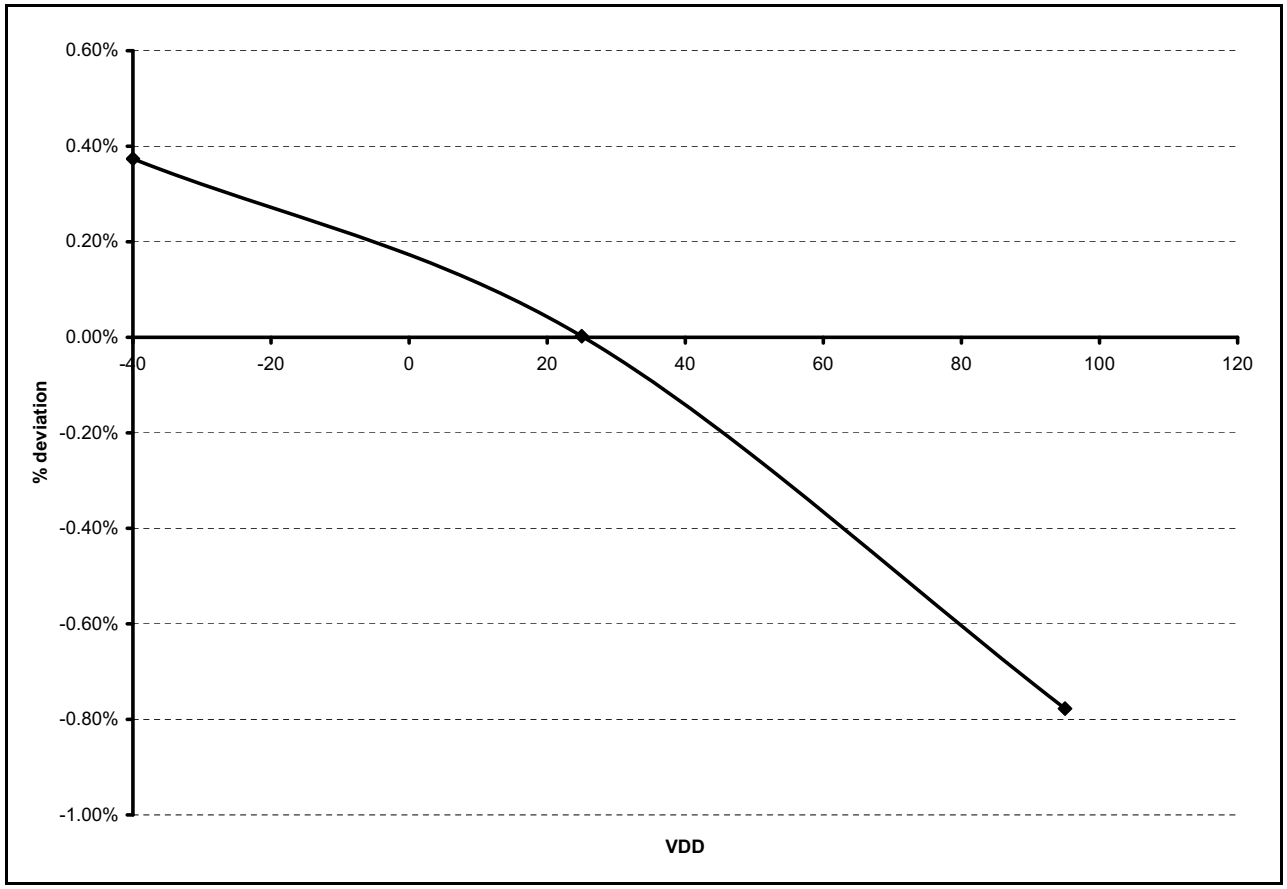


Figure 15. Deviation of DCO Output Across Temperature at V_{DD} = 3.0 V

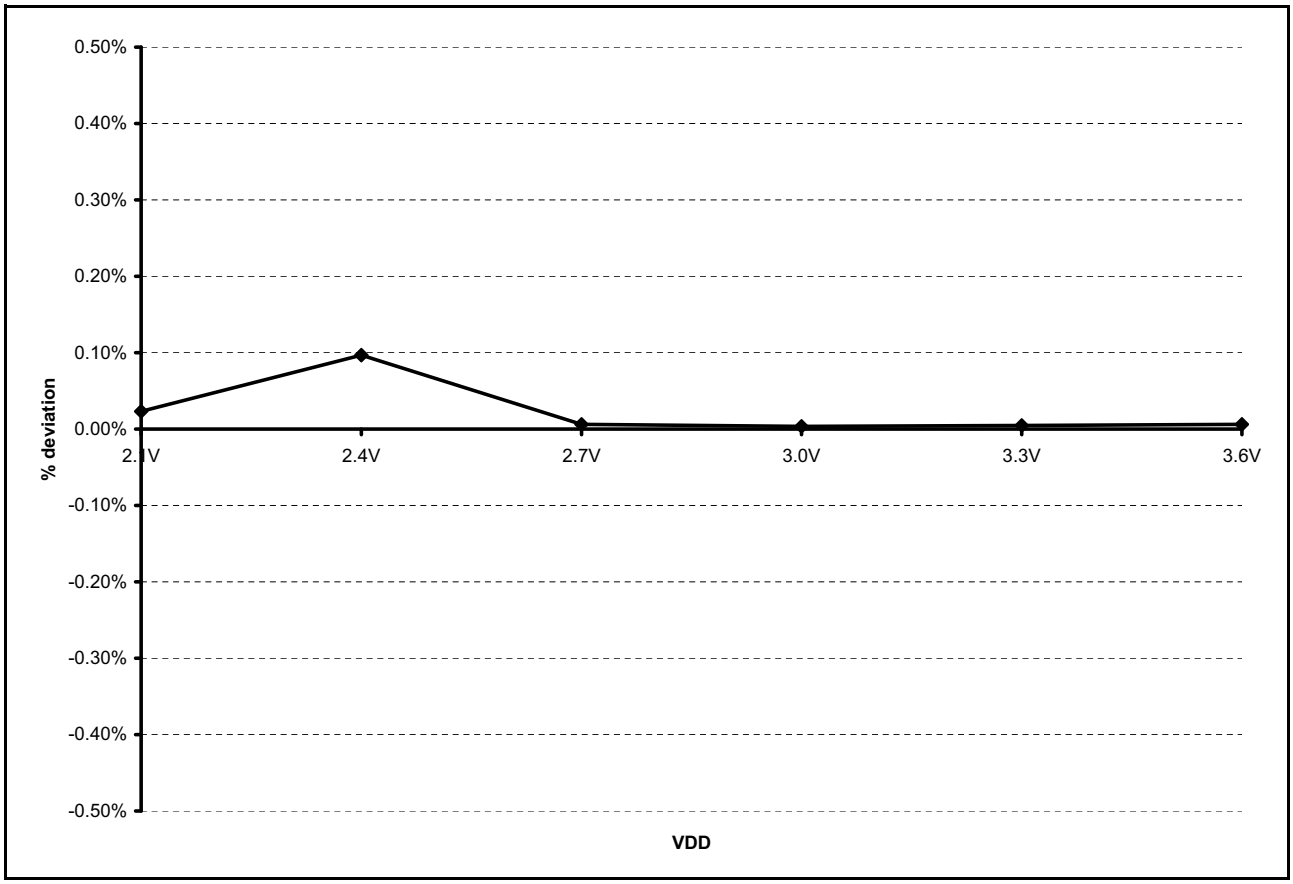


Figure 16. Deviation of DCO Output Across V_{DD} at 25°C

3.10 AC Characteristics

This section describes timing characteristics for each peripheral system.

3.10.1 Control Timing

Table 13. Control Timing

Num	C	Rating	Symbol	Min	Typ[1]	Max	Unit
1	D	Bus frequency (t_{cyc} = 1/f_{Bus}) $V_{DD} \geq 1.8V$ $V_{DD} > 2.1V$ $V_{DD} > 2.4V$	f_{Bus}	dc	— — —	10 20 25.165	MHz
2	D	Internal low power oscillator period	t_{LPO}	700	—	1300	µs
3	D	External reset pulse width[2]	t_{extrst}	100	—	—	ns
4	D	Reset low drive	t_{rstdrv}	34 x t_{cyc}	—	—	ns
5	D	BKGD/MS setup time after issuing background debug force reset to enter user or BDM modes	t_{MSSU}	500	—	—	ns
6	D	BKGD/MS hold time after issuing background debug force reset to enter user or BDM modes [3]	t_{MSH}	100	—	—	µs

Table 13. Control Timing (continued)

Num	C	Rating	Symbol	Min	Typ[1]	Max	Unit
7	D	IRQ pulse width Asynchronous path[2] Synchronous path[4]	t_{ILIH}, t_{IHIL}	100 1.5 x t_{cyc}	— —	— —	ns
8	D	Keyboard interrupt pulse width Asynchronous path[2] Synchronous path[4]	t_{ILIH}, t_{IHIL}	100 1.5 x t_{cyc}	— —	— —	ns
9	C	Port rise and fall time — Low output drive (PTxDS = 0) (load = 50 pF)[5] Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1)	t_{Rise}, t_{Fall}	— —	8 31	— —	ns
		Port rise and fall time — High output drive (PTxDS = 1) (load = 50 pF) Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1)	t_{Rise}, t_{Fall}	— —	7 24	— —	ns
10		Voltage regulator recovery time	t_{VRR}	—	4	—	µs

1 Typical values are based on characterization data at V_{DD} = 3.0V, 25°C unless otherwise stated.

2 This is the shortest pulse that is guaranteed to be recognized as a reset or interrupt pin request. Shorter pulses are not guaranteed to override reset requests from internal sources.

3 To enter BDM mode following a POR, BKGD/MS should be held low during the power-up and for a hold time of t_{MSH} after V_{DD} rises above V_{LVD}.

4 This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized in that case.

5 Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels. Temperature range –40°C to 85°C.

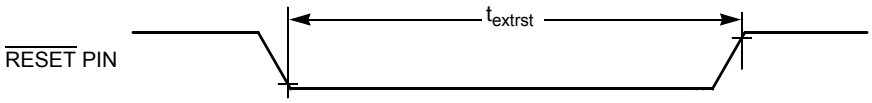


Figure 17. Reset Timing

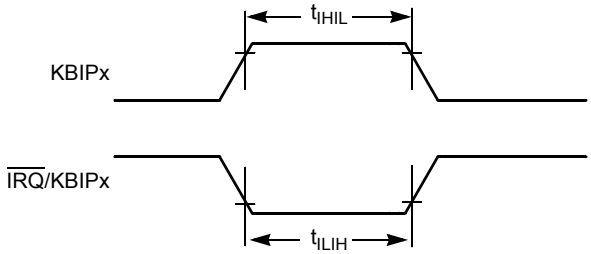
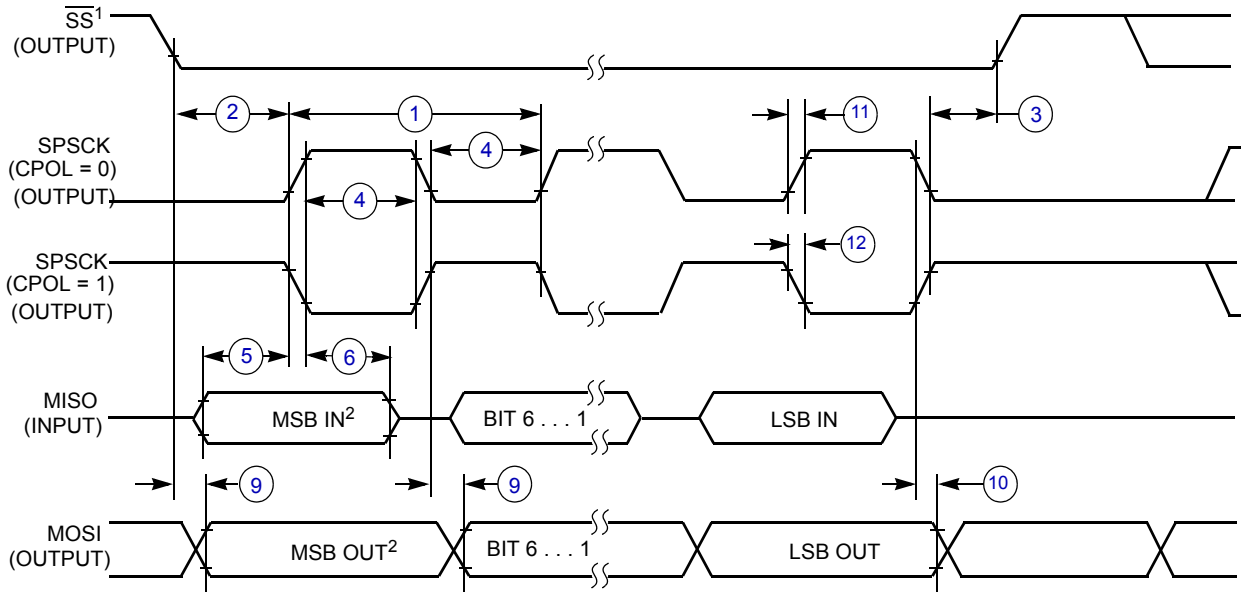
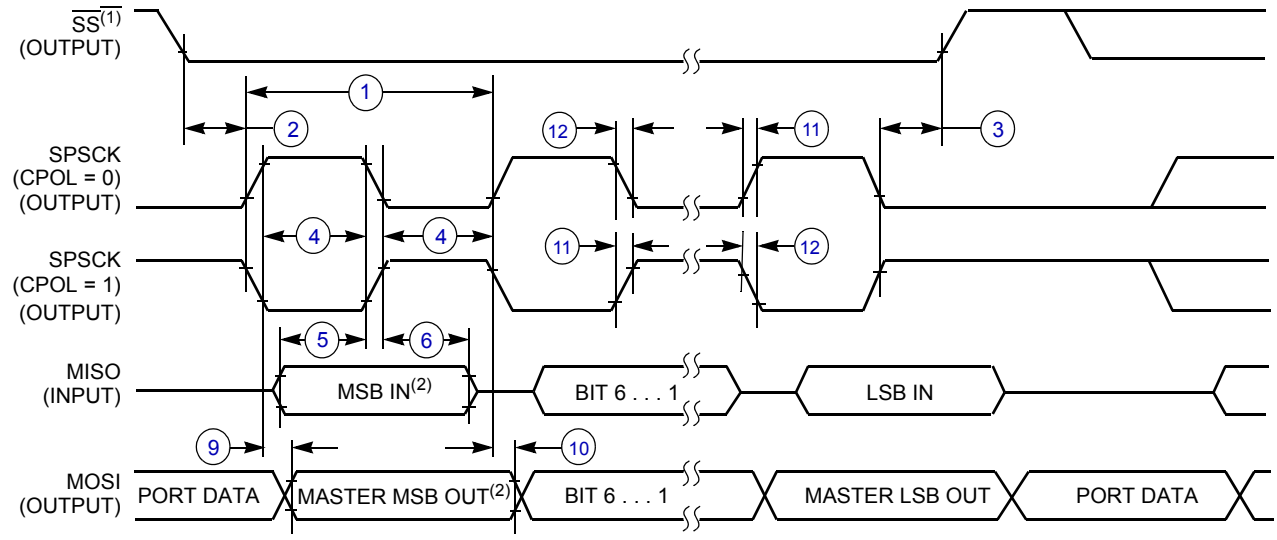


Figure 18. IRQ/KBIPx Timing



NOTES:
1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 21. SPI Master Timing (CPHA = 0)



NOTES:
1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 22. SPI Master Timing (CPHA =1)

4 Ordering Information

This section contains ordering information for MC9S08QE128, MC9S08QE96, and MC9S08QE64 devices.

Table 20. Ordering Information

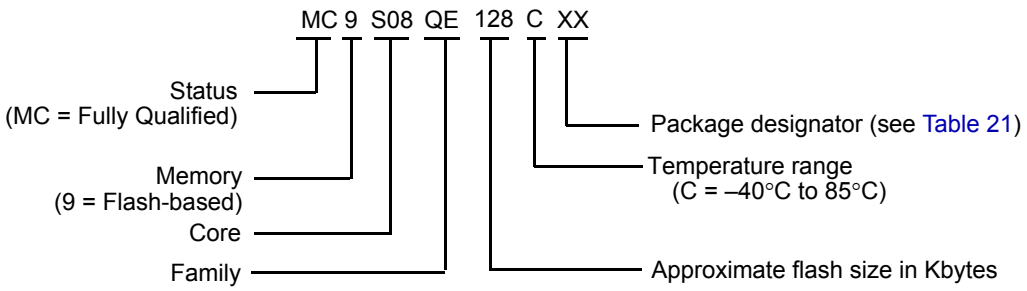
Freescale Part Number[1]	Memory		Temperature range (°C)	Package[2]
	Flash	RAM		
MC9S08QE128CLK	128K	8K	-40 to +85	80 LQFP
MC9S08QE128CLH			-40 to +85	64 LQFP
MC9S08QE128CFT			-40 to +85	48 QFN
MC9S08QE128CLD			-40 to +85	44 LQFP
MC9S08QE96CLK	96K	6K	-40 to +85	80 LQFP
MC9S08QE96CLH			-40 to +85	64 LQFP
MC9S08QE96CFT			-40 to +85	48 QFN
MC9S08QE96CLD			-40 to +85	44 QFP
MC9S08QE64CLH	64K	4K	-40 to +85	64 LQFP
MC9S08QE64CFT			-40 to +85	48 QFN
MC9S08QE64CLD			-40 to +85	44 QFP
MC9S08QE64CLC			-40 to +85	32 LQFP

1 See the reference manual, *MC9S08QE128RM*, for a complete description of modules included on each device.

2 See Table 21 for package information.

4.1 Device Numbering System

Example of the device numbering system:

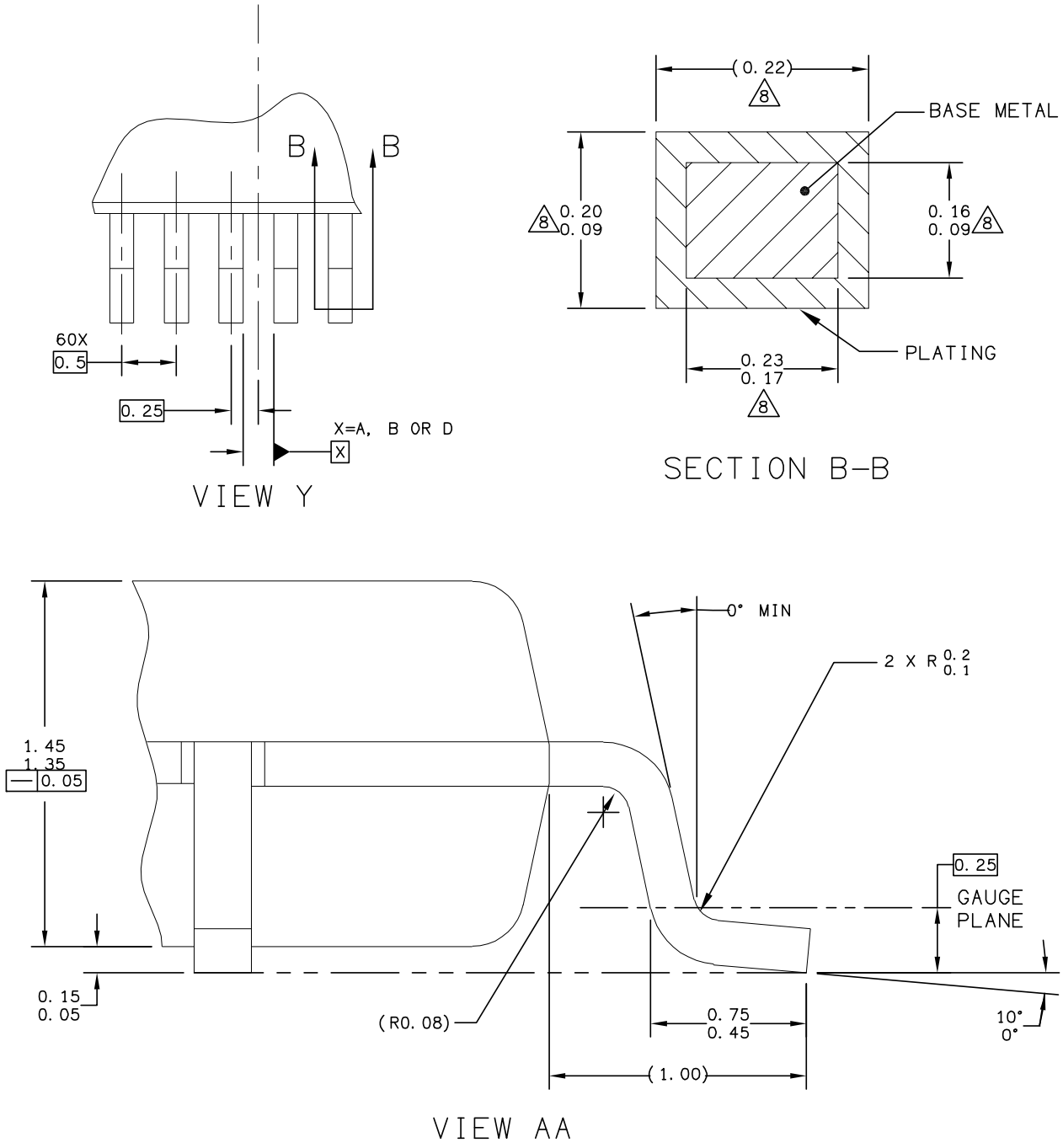


5 Package Information

The below table details the various packages available.

Table 21. Package Descriptions

Pin Count	Package Type	Abbreviation	Designator	Case No.	Document No.
80	Low Quad Flat Package	LQFP	LK	917A	98ASS23237W
64	Low Quad Flat Package	LQFP	LH	840F	98ASS23234W
48	Quad Flat No-Leads	QFN	FT	1314	98ARH99048A
44	Low Quad Flat Package	LQFP	LD	824D	98ASS23225W
32	Low Quad Flat Package	LQFP	LC	873A	98ASH70029A



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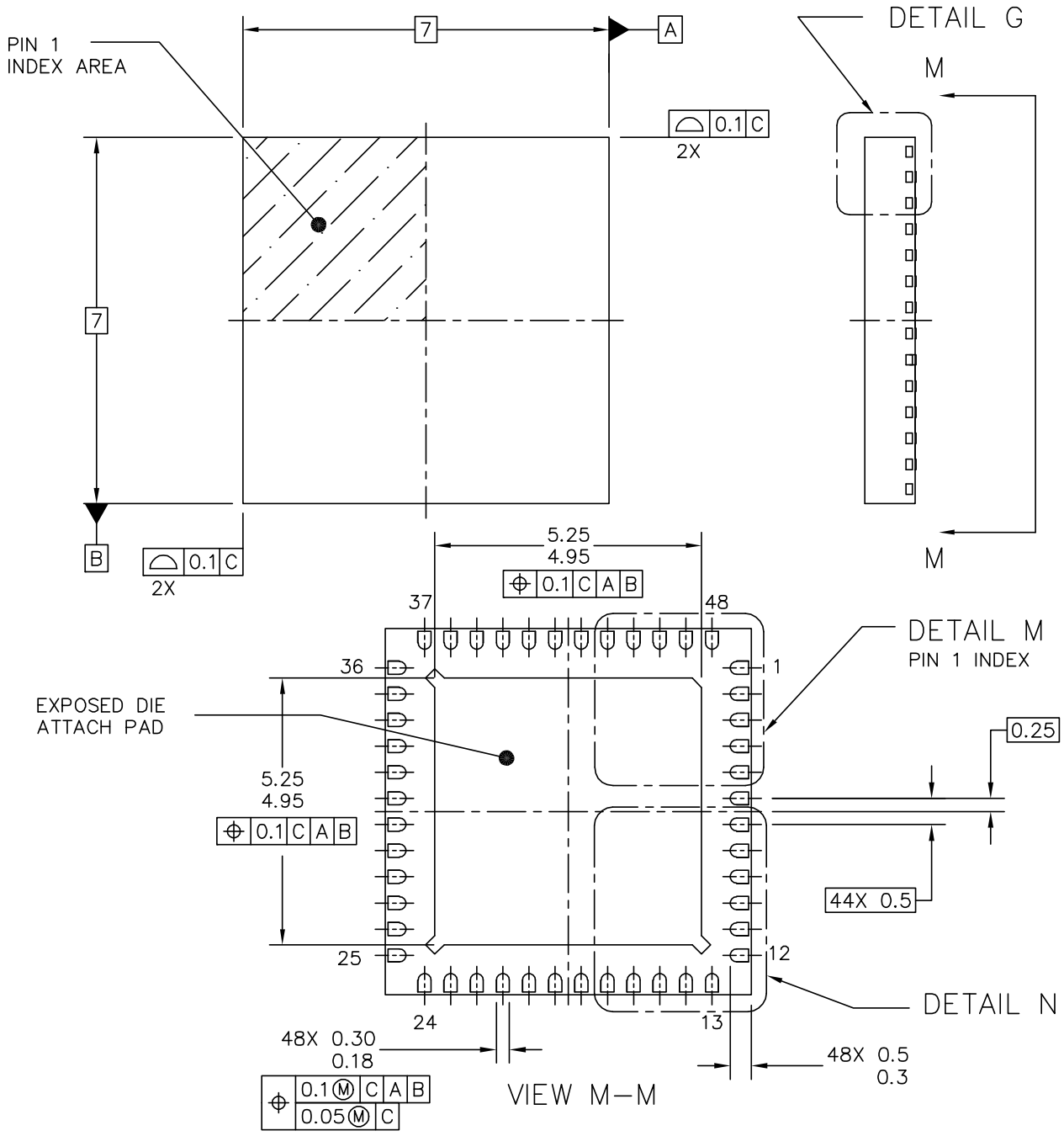
TITLE: 64LD LQFP, 10 X 10 X 1.4 PKG, 0.5 PITCH, CASE OUTLINE	DOCUMENT NO: 98ASS23234W	REV: D
	CASE NUMBER: 840F-02	06 APR 2005
	STANDARD: JEDEC MS-026 BCD	

Figure 28. 64-pin LQFP Package Drawing (Case 840F, Doc #98ASS23234W), Sheet 2 of 3



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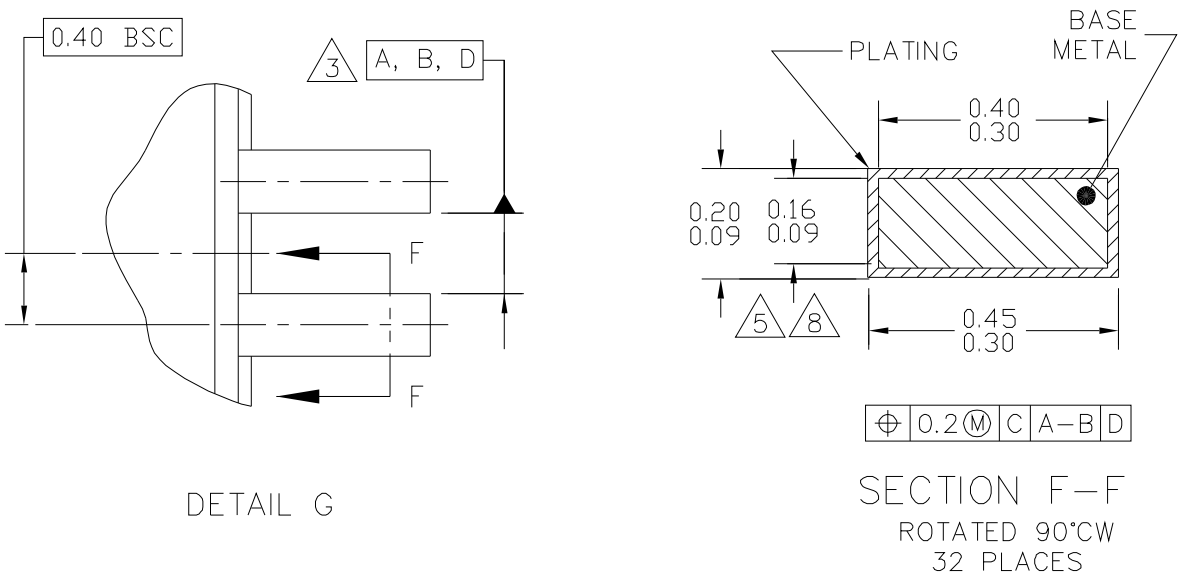
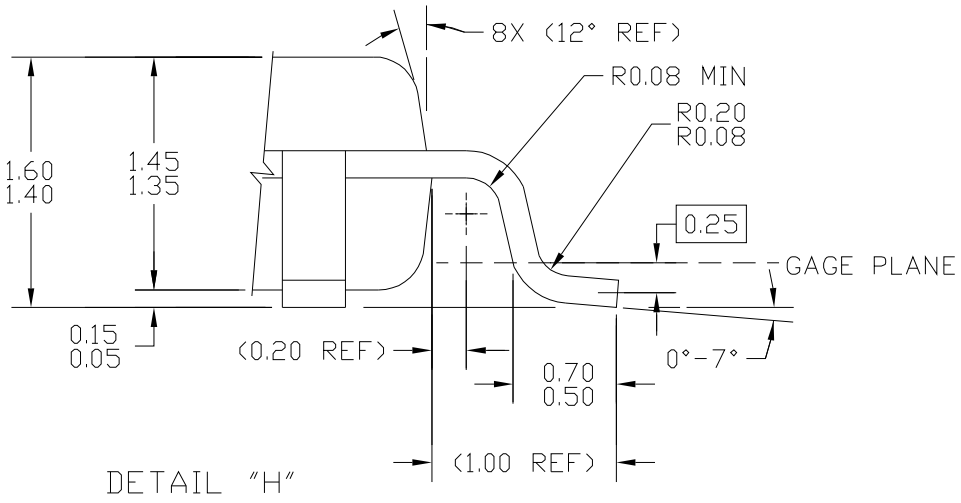
TITLE: THERMALLY ENHANCED QUAD FLAT NON–LEADED PACKAGE (QFN) 48 TERMINAL, 0.5 PITCH (7 X 7 X 1)	DOCUMENT NO: 98ARH99048A	REV: F
	CASE NUMBER: 1314–05	05 DEC 2005
	STANDARD: JEDEC–MO–220 VKKD–2	

Figure 30. 48-pin QFN Package Drawing (Case 1314, Doc #98ARH99048A), Sheet 1 of 3





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TITLE: LOW PROFILE QUAD FLAT PACK (LQFP) 32 LEAD, 0.8 PITCH (7 X 7 X 1.4)	DOCUMENT NO: 98ASH70029A	REV: D
	CASE NUMBER: 873A-03	19 MAY 2005
	STANDARD: JEDEC MS-026 BBA	

Figure 37. 32-pin LQFP Package Drawing (Case 873A, Doc #98ASH70029A), Sheet 2 of 3

NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.

2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5–1994.

3. DATUMS A, B, AND D TO BE DETERMINED AT DATUM PLANE H.

4. DIMENSIONS TO BE DETERMINED AT SEATING PLANE DATUM C.

5. DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE MAXIMUM DIMENSION BY MORE THAN 0.08 MM. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD OR PROTRUSION: 0.07 MM.

6. DIMENSIONS DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 MM PER SIDE. DIMENSIONS ARE MAXIMUM PLASTIC BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH.

7. EXACT SHAPE OF EACH CORNER IS OPTIONAL.

8. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.1 MM AND 0.25 MM FROM THE LEAD TIP.

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TITLE: LOW PROFILE QUAD FLAT PACK (LQFP) 32 LEAD, 0.8 PITCH (7 X 7 X 1.4)	DOCUMENT NO: 98ASH70029A	REV: D
	CASE NUMBER: 873A-03	19 MAY 2005
	STANDARD: JEDEC MS-026 BBA	

Figure 38. 32-pin LQFP Package Drawing (Case 873A, Doc #98ASH70029A), Sheet 3 of 3

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